

#2/Pre Amended
5/2/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re New Patent Application of)
Shunpei YAMAZAKI et al.)
Japanese Priority Application No. 2001-040848) Attn: Applications
Japanese Priority Date: February 16, 2001) Branch
For: METHOD OF MANUFACTURING)
A SEMICONDUCTOR DEVICE) Date: February 14, 2002

PRELIMINARY AMENDMENT

Honorable Commissioner for Patents and Trademarks
Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows:

IN THE CLAIMS:

Please cancel claims 1-106 and add new claims 107-211 as follows:

--107. A method of manufacturing a semiconductor device comprising the steps of:

adding a metal element to a first semiconductor film comprising amorphous silicon over a substrate;

crystallizing the first semiconductor film to form a first crystalline semiconductor film;

forming a barrier layer on the first crystalline semiconductor film;

forming a second semiconductor film on the barrier layer;

forming a third semiconductor film containing one conductive type impurity element on the second semiconductor film;

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